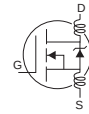


Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.070	—	V/°C	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.027	W	$V_{GS} = 10V, I_D = 25A$ ④
		—	—	0.030		$V_{GS} = 5.0V, I_D = 25A$ ④
		—	—	0.040		$V_{GS} = 4.0V, I_D = 21A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	21	—	—	S	$V_{DS} = 25V, I_D = 25A$ ⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	48	nC	$I_D = 25A$
Q_{gs}	Gate-to-Source Charge	—	—	8.6		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	25		$V_{GS} = 5.0V$, See Fig. 6 and 13 ④ ⑦
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	84	—		$I_D = 25A$
$t_{d(off)}$	Turn-Off Delay Time	—	26	—		$R_G = 3.4\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	15	—		$R_D = 1.1\Omega$, See Fig. 10 ④ ⑦
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1700	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	400	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	150	—		$f = 1.0MHz$, See Fig. 5 ⑦



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	42	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 25A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	80	120	ns	$T_J = 25^\circ\text{C}, I_F = 25A$
Q_{rr}	Reverse Recovery Charge	—	210	320	nC	$di/dt = 100A/\mu s$ ④ ⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu H$
 $R_G = 25\Omega, I_{AS} = 25A$. (See Figure 12)
- ③ $I_{SD} \leq 25A$, $di/dt \leq 270A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑦ Uses IRLZ44N data and test conditions.

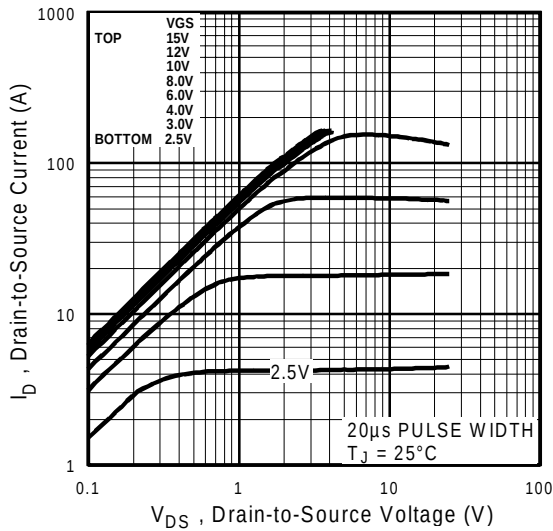


Fig 1. Typical Output Characteristics

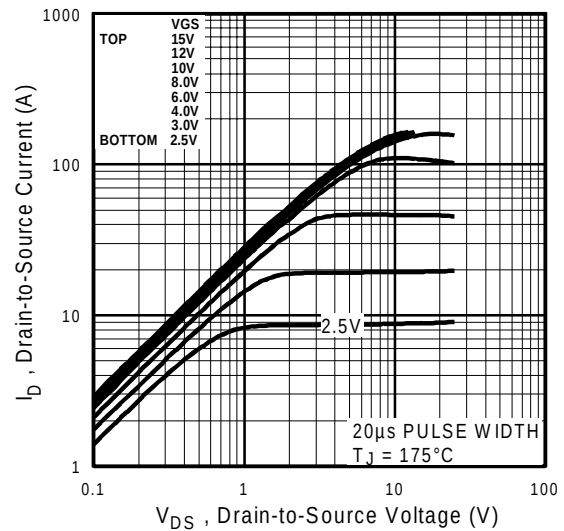


Fig 2. Typical Output Characteristics

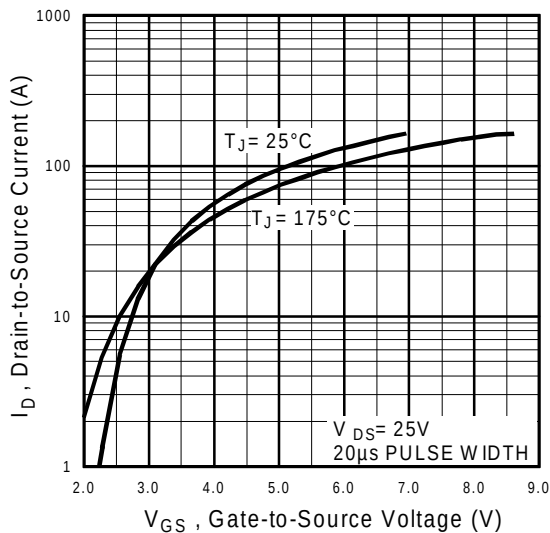


Fig 3. Typical Transfer Characteristics

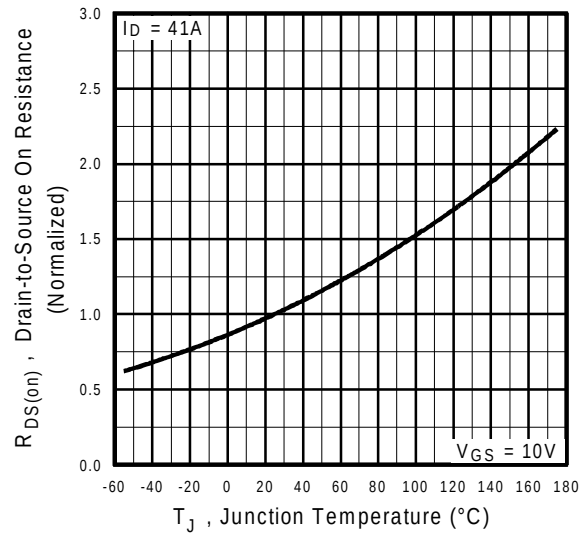


Fig 4. Normalized On-Resistance
Vs. Temperature

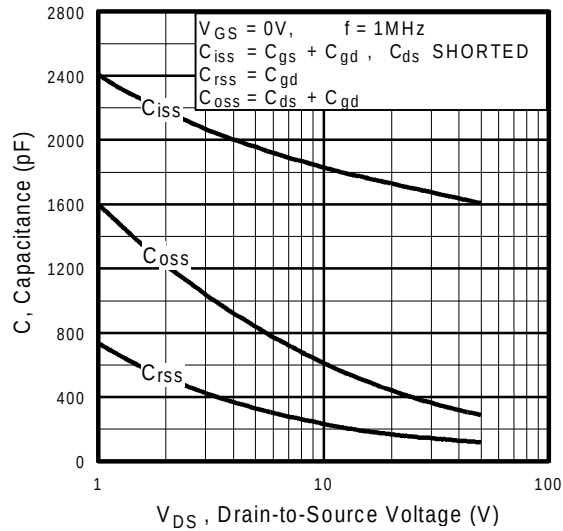


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

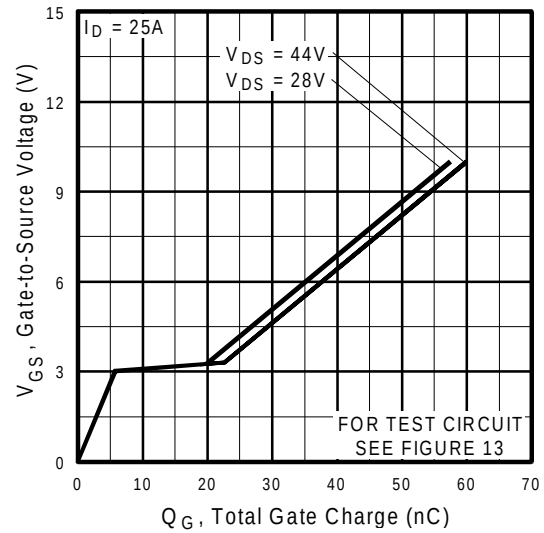


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

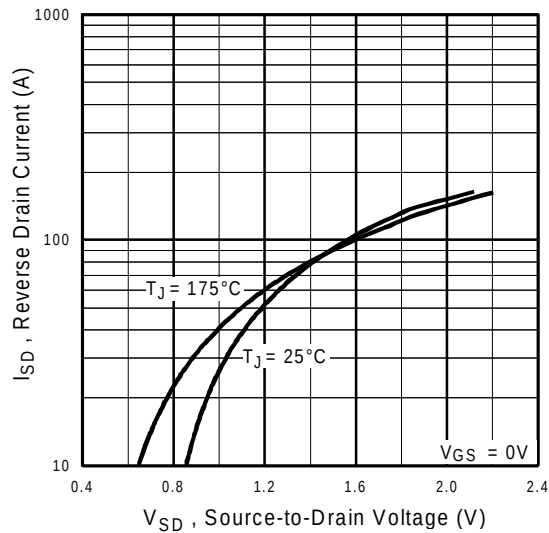


Fig 7. Typical Source-Drain Diode Forward Voltage

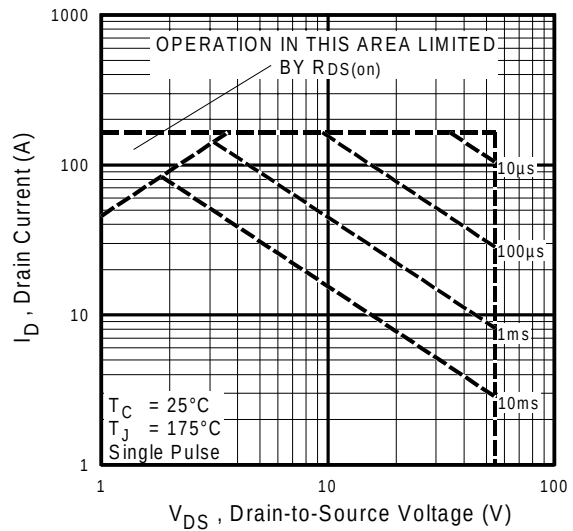


Fig 8. Maximum Safe Operating Area

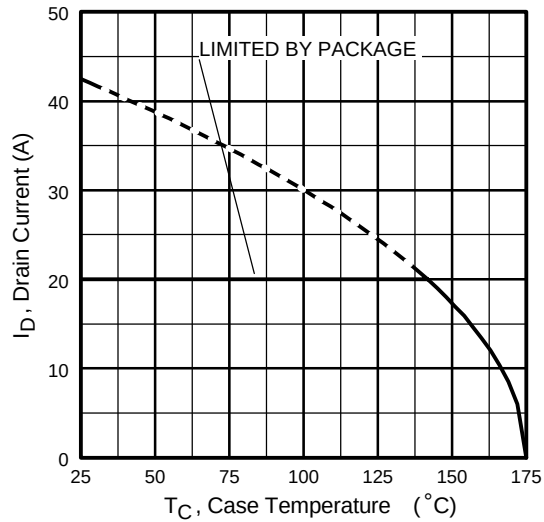


Fig 9. Maximum Drain Current Vs. Case Temperature

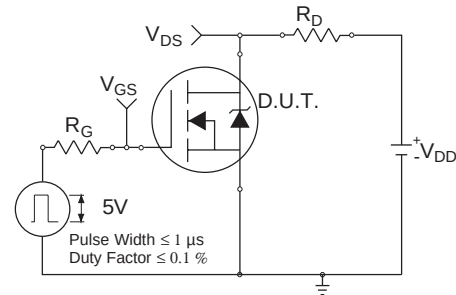


Fig 10a. Switching Time Test Circuit

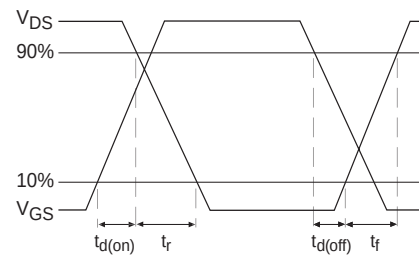


Fig 10b. Switching Time Waveforms

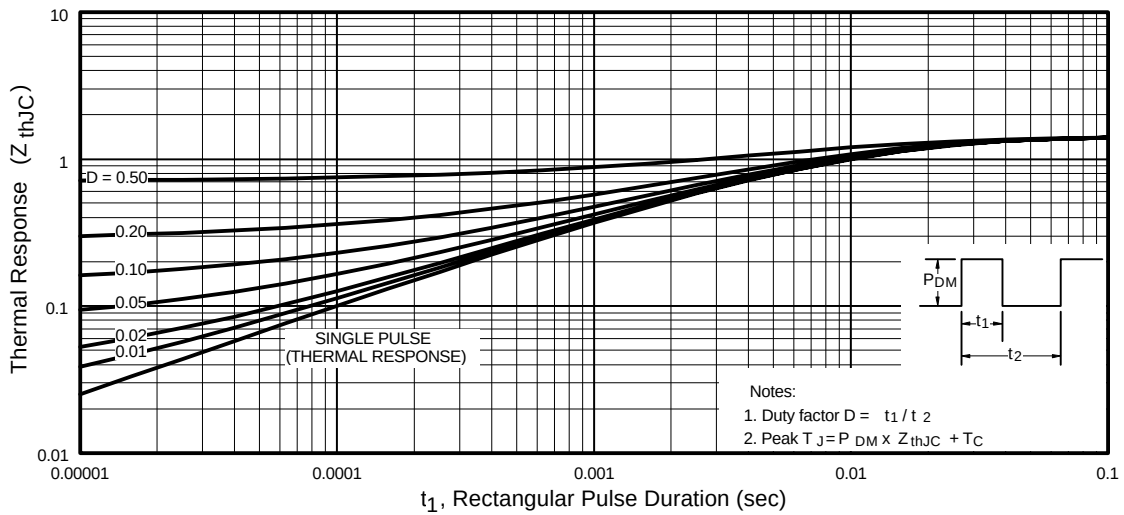


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

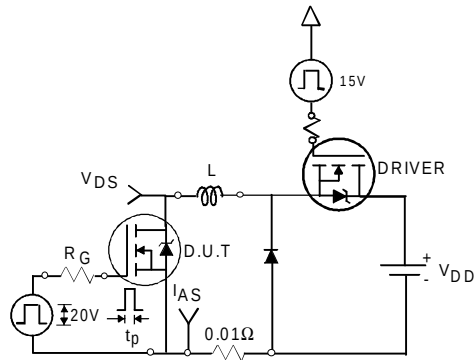


Fig 12a. Unclamped Inductive Test Circuit

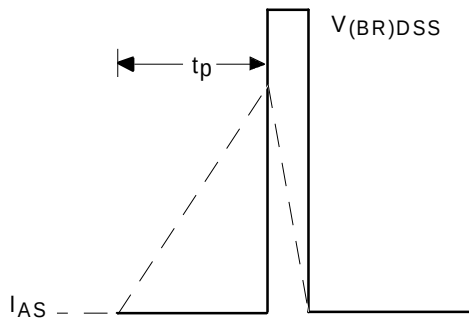


Fig 12b. Unclamped Inductive Waveforms

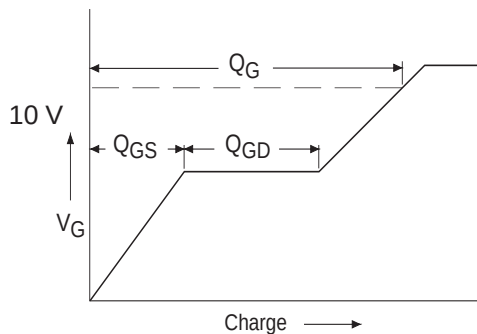


Fig 13a. Basic Gate Charge Waveform

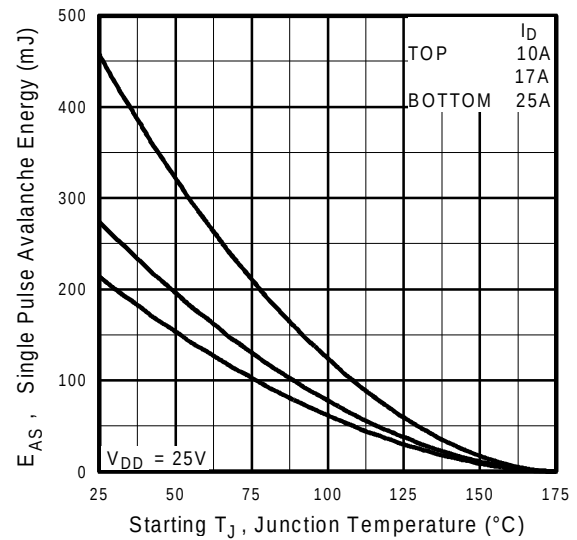


Fig 12c. Maximum Avalanche Energy
Vs. Drain Current

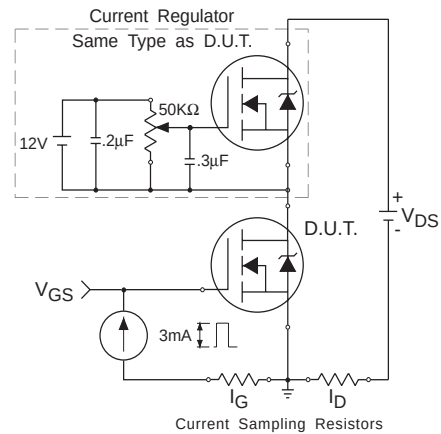
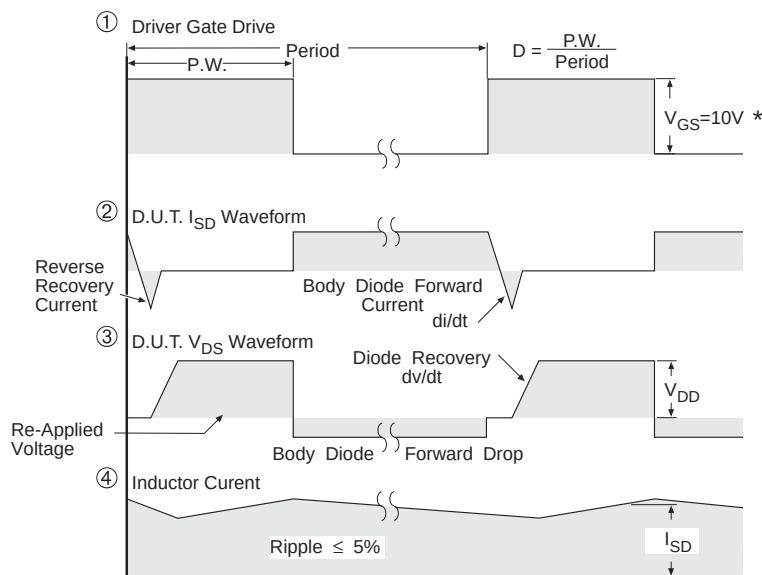
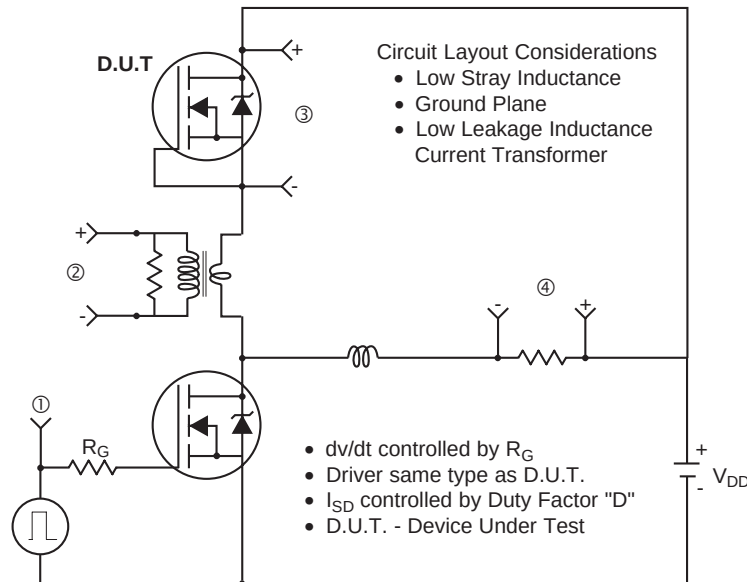


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

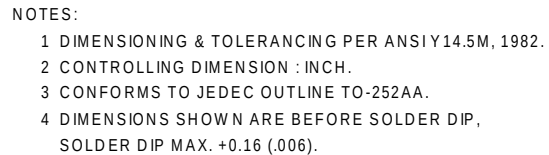


* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



TO-252AA (D-PARK)

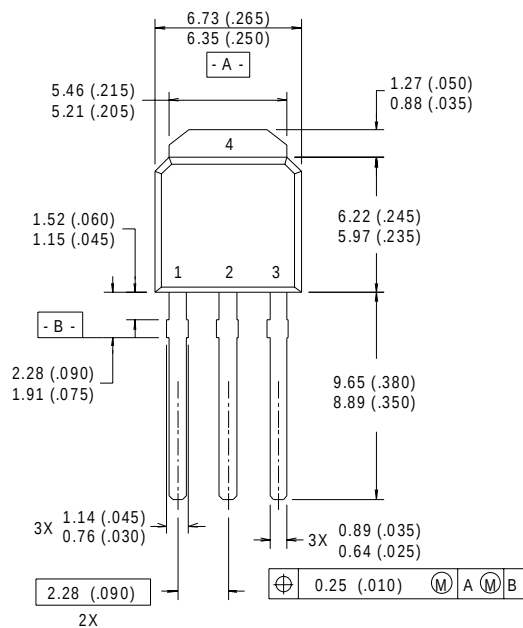
Diagram illustrating the markings on the IRFR120 MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the stylized logo on the top left of the package.
- FIRST PORTION OF PART NUMBER**: Points to the "IRFR" text on the top right of the package.
- SECOND PORTION OF PART NUMBER**: Points to the "120" text on the bottom right of the package.
- ASSEMBLY LOT CODE**: Points to the "9U 1P" text on the bottom left of the package.

Package Outline

TO-251AA Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE
- 4 - DRAIN

NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 CONFORMS TO JEDEC OUTLINE TO-252AA.
- 4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP, SOLDER DIP MAX. +0.16 (.006).

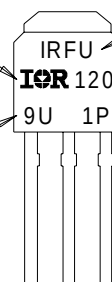
Part Marking Information

TO-251AA (I-PARK)

EXAMPLE : THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 9U1P

INTERNATIONAL
RECTIFIER
LOGO

ASSEMBLY
LOT CODE



FIRST PORTION
OF PART NUMBER

SECOND PORTION
OF PART NUMBER

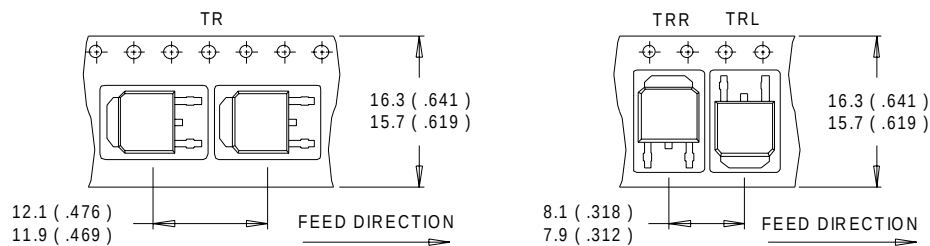
IRLR/U2905

International
IR Rectifier

Tape & Reel Information

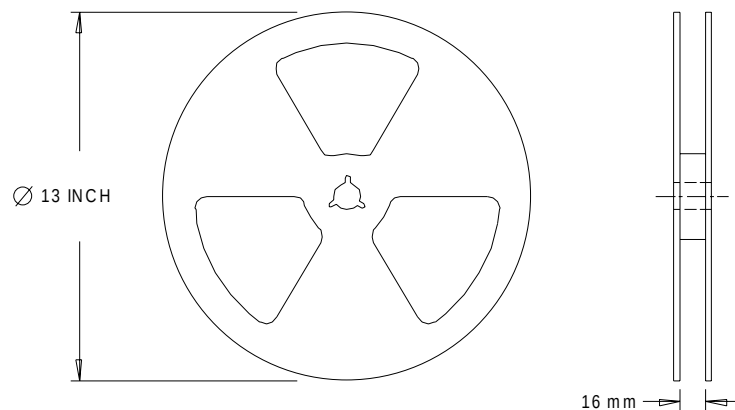
TO-252AA

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.

Data and specifications subject to change without notice. 12/00

www.irf.com

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>